Silicon PNP Power Transistors 2SB1230

DESCRIPTION

·With TO-3PN package
·Wide area of safe operation
·Complement to type 2SD1840
·Low collector saturation voltage

APPLICATIONS

·Motor drivers,relay drivers,converters and other general high-current switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

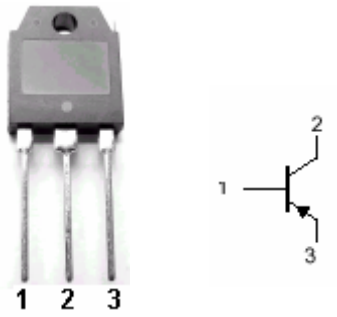

Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Tc=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-110	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-6	V
I_C	Collector current		-15	A
I_{CM}	Collector current -peak		-25	A
I_B	Base current		-5	A
P_C	Collector power dissipation	T_a=25□	3.0	W
		T_C=25□	100	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-5mA;R_{BE}=∞	-100			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	I_C=-1mA; I_E=0	-110			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=-1mA; I_C=0	-6			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-6A; I_B=-0.6A			-0.8	V
$V_{BE\ sat}$	Base-emitter saturation voltage	I_C=-6A; I_B=-0.6A			-1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=-100V; I_E=0			-100	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-5V; I_C=0			-100	μA
h_{FE-1}	DC current gain	I_C=-1.5A ; V_{CE}=-2V	50		140	
h_{FE-2}	DC current gain	I_C=-6A ; V_{CE}=-2V	20			

◆ **h_{FE-1} Classifications**

P	Q
50-100	70-140

PACKAGE OUTLINE

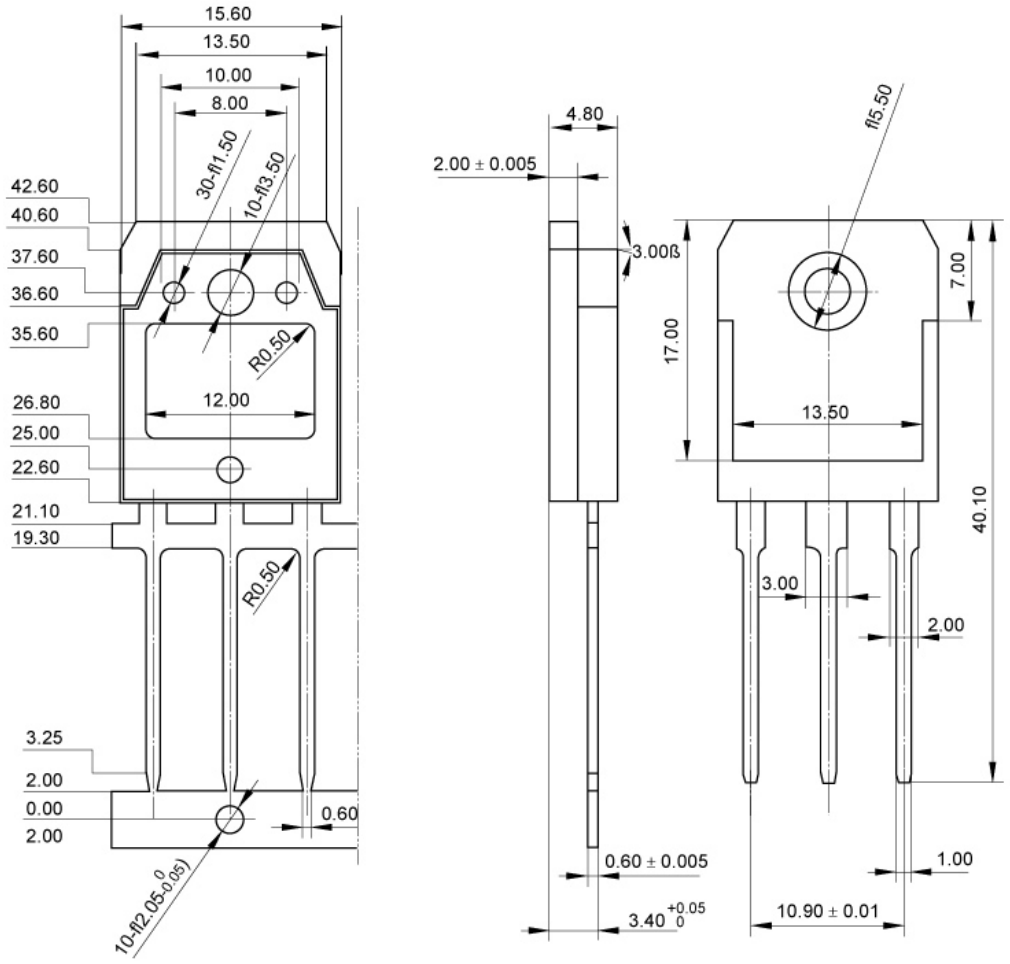

Fig.2 outline dimensions